

High-reliability discrete products and engineering services since 1977

### SILICON BIDIRECTIONAL THYRISTORS

## FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
  - Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak repetitive off-state voltage <sup>(1)</sup>			
(T <sub>J</sub> = 100°C)			
MAC10-1,MAC11-1		25	
MAC10-2,MAC11-2		50	
MAC10-3,MAC11-3	V <sub>DRM</sub>	100	Volts
MAC10-4, MAC11-4		200	
MAC10-5,MAC11-5		300	
MAC10-6,MAC11-6		400	
MAC10-7,MAC11-7		500	
MAC10-8,MAC11-8		600	
RMS on-state current (T <sub>c</sub> = 75°C)	I <sub>T(RMS)</sub>	10	Amps
Peak non-repetitive surge current			A
(1 cycle, 60Hz, T <sub>J</sub> = -40 to + 100°C)	ITSM	100	Amps
Circuit fusing considerations ( $T_J$ = -40 to + 100°C, t = 8.3ms)	l <sup>2</sup> t	40	A <sup>2</sup> s
Peak gate power	P <sub>GM</sub>	10	Watts
Average gate power	P <sub>G(AV)</sub>	0.5	Watts
Peak gate current	I <sub>GM</sub>	2	Amps
Operating junction temperature range	Tj	-40 to +100	°C
Storage temperature range	T <sub>stg</sub>	-40 to +150	°C
Mounting torque (6-32 screw) <sup>(2)</sup>		8	In. lb.

Note 1: Ratings apply for open gate conditions. Thyristor devices shall not be tested with a constant current source for blocking capability such that the voltage applied exceeds the rated blocking voltage. Note 2: Torque rating applies with use of torque washer. Mounting torque in excess of 8 in. lb. does not appreciably lower case to sink thermal resistance. Anode lead and heatsink contact pad are common. \* Soldering temperatures shall not exceed 200°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Maximum	Unit
Thermal resistance, junction to case	R <sub>ejc</sub>	2.0	°C/W
Thermal resistance, junction to ambient	R <sub>eja</sub>	50	°C/W

### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise specified)

Characteristic	Symbol	Min	Тур.	Max	Unit
Peak blocking current (either direction)					m 4
( $V_D$ = Rated $V_{DRM}$ , gate open, $T_J$ = 100°C)	IDRM	-	-	2.0	ma
Peak on-state voltage (either direction)	V <sub>TM</sub>				Volta
(I <sub>TM</sub> = 14A peak)		-	1.3	1.8	VOILS
Gate trigger current (continuous dc)					
$(V_{D} = 12V, R_{L} = 100\Omega)$	1				m۸
MT2(+),G(+); MT2(-),G(-) , MAC10, MAC11	IGT	-	-	50	ША
MT2(+),G(-); MT2(-), G(+), MAC10		-	-	75	



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Gate trigger voltage (continuous dc)					
$(V_{D} = 12V, R_{L} = 100\Omega)$	V				Volte
MT2(+),G(+); MT2(-),G(-) , MAC10, MAC11	V GT	-	0.9	2.0	VOILS
MT2(+),G(-); MT2(-), G(+), MAC10		-	1.0	2.5	
Gate trigger voltage (continuous dc)	N				Volte
(V_D = Rated V_{DRM}, R_L = 100 \Omega, T_J = 100 °C) All modes	VGD	0.2	-	-	VOILS
Holding current (either direction)	I <sub>H</sub>				mA
( $V_D$ = 12V, $I_{TM}$ = 100mA, gate open)		-	-	50	
Gate controlled turn-on time	t <sub>on</sub>				μs
(I <sub>TM</sub> = 14A, I <sub>GT</sub> = 100mA)		-	1.5	-	
Blocking voltage application rate at commutation	dv/dt				V/µs
(@ $V_{DRM,} T_J = 75^{\circ}C$ , gate open)		-	5.0	-	

### MECHANICAL CHARACTERISTICS

Case	TO-127
Marking	Alpha-numeric
Pin out	See below

С



		TO	-127		
	Inches		Millimeters		
	Min	Max	Min	Max	
Α	0.635	0.645	16.130	16.380	
В	0.495	0.505	12.570	12.830	
С	0.125	0.135	3.180	3.430	
D	0.043	0.049	1.090	1.240	
F	0.138	0.148	3.510	3.760	
G	0.166 BSC		4.220	BSC	
Н	0.105	0.115	2.670	2.920	
J	0.032	0.034	0.813	0.864	
K	0.595	0.645	15.110	16.380	
М	9° TYP		9° 1	ГҮР	
Q	0.185	0.195	4.700	4.950	
R	0.075	0.085	1.910	2.160	
U	0.245	0.255	6.220	6.480	
۷	0.080	(#2)	2.030	(72)	



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FIGURE 4 - POWER DISSIPATION





FIGURE 6 - TYPICAL GATE TRIGGER CURRENT





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FIGURE 10 - THERMAL RESPONSE

